ST 2SC930C1...F1

NPN Silicon Epitaxial Planar Transistor

for FM RF amp, mixer, osc, converter and IF amplifier.

The transistor is subdivided into four groups C1, D1, E1 and F1, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	20	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	30	mA
Power Dissipation	P _{tot}	250	mW
Junction Temperature	T _j	125	°С
Storage Temperature Range	Ts	-55 to +125	°С







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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =6V, I _C =1mA					
Current Gain Group C1	h _{FE}	40	-	80	-
D1	h _{FE}	60	-	120	-
E1	h _{FE}	100	-	200	-
F1	h _{FE}	160	-	320	-
Collector Cutoff Current					
at V _{CB} =10V	I _{CBO}	-	-	1	μΑ
Emitter Cutoff Current					
at V _{EB} =4V	I _{EBO}	-	-	1	μΑ
Gain Bandwidth Product					
at V _{CE} =6V, I _C =1Ma	f _T	170	300	-	MHz
Reverse Transfer Capacitance					
at V _{CB} =6V, f=1MHz	Cre	1	1.3	1.8	pF
Base to Collector Time Constant					
at V _{CB} =6V, I _C =1mA, f=31.9MHz	Rbb • Cc	-	20	36	ps
Noise Figure					
at V_{CB} =6V, I_C =1mA, f=100MHz	NF	-	4	-	dB
Turn-on Time					
at V_{IN} =+12V, V_{BE} =-3V,appointed circuit	t _{on}	-	30	-	ns
Turn-off Time					
at V _{IN} =-12V, V _{BE} =+3V, appointed circuit	t _{off}	-	30	-	ns









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